

a

b

100 μm

Fig. 1. Nomarski photographs of the same area of a 4H-SiC sample with two different epilayers. (a) first epilayer, (b) second epilayer, after first was removed. Note triangular features growing from scratches.

a

b

100 μm

Fig. 2. Nomarski photographs of the same area of a 6H-SiC sample with two different epilayers. (a) first epilayer, (b) second epilayer, after first was removed. Boxes indicate growth pits common to both epilayers.

a

b

100 μm

Fig. 3. Nomarski photographs of 12-mm-thick 4H-SiC epilayers grown on 4H-SiC substrates with tilt angles of (a) 3.5° and (b) 8° .

a

b

c

Fig. 4. Nomarski photographs of 6H-SiC epilayers grown with Si/C ratio = 0.19, but with different silane and propane concentrations. (a) [Si] = 170 ppm, (b) [Si] = 200 ppm, (c) [Si] = 220 ppm.